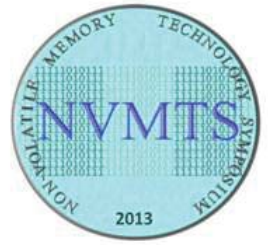
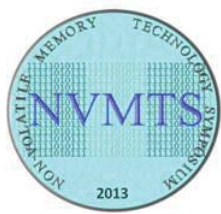


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SUBMITTED POSTERS

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P-1	Xiaomin Cheng , <i>Huazhong University of Science and Technology</i> Three-Dimensional Simulation and Analysis of Phase Change Memory Cell with Asymmetric Structure
P-2	Thomas Dunn , <i>University of Minnesota</i> Optimization of spin-torque switching using AC and DC pulses
P-3	Will Echtenkamp , <i>University of Nebraska, Lincoln</i> Electric Control of Exchange Bias Training
P-4	Xuanyao Fong , <i>Purdue University</i> On-chip Multi-terminal Spin-Transfer Torque MRAM
P-5	Ruomeng Huang , <i>University of Southampton</i> Determination of Specific Contact Resistance of $\text{Ge}_2\text{Sb}_2\text{Te}_5$ Phase Change Materials by Spacer Etched Nanowires
P-6	Mahdi Jamali , <i>University of Minnesota</i> Thickness dependence of the spin current pumping from CoFeB into Ta
P-7	Mahdi Jamali , <i>University of Minnesota</i> Sub-200 ps STT switching in thermally stable magnetic tunnel junctions with interface perpendicular anisotropy
P-8	JinWon Jung , <i>Tohoku University</i> Experimental Confirmation of Spin Filtering Interface-Resistance
P-9	Angeline Klemm , <i>University of Minnesota</i> Voltage Controlled Magnetic Tunnel Junction Based Logic Architecture
P-10	Angeline Klemm , <i>University of Minnesota</i> Spin Transfer Torque Programming and Clock Field Effects for Dipole Coupled Nanomagnetic Arrays
P-11	Tian Lan , <i>Huazhong University of Science and Technology</i> Fabrication independent from lithography resolution for lateral phase-change random access memory
P-12	Hochul Lee , <i>University of California, Los Angeles</i> Design of a High Speed and Low Power Sense Amplifier for Magnetoelectric Random Access Memory (MeRAM)
P-13	Lu Liu , <i>Huazhong University of Science and Technology</i> Improved Memory Window of MONOS Capacitor Memory with GdON as Charge Storage Layer
P-14	Tong Liu , <i>Virginia Polytechnic Institute and State University</i> Analysis of Multilevel Capability of a Filamentary Resistive Memory Cell



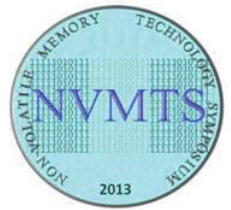
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P-15	Yang Lu , <i>University of Pennsylvania</i> A Serial Load Circuit Model for Low Resistance State in Resistance Switching Memory
P-16	Yang Lv , <i>University of Minnesota</i> Spin-Transfer Torque Switching Above Room-Temperature
P-17	Nicolas Onofrio , <i>Purdue University</i> Reactive molecular dynamics of switching in conductive bridge random access memory
P-18	Biplab Sarkar , <i>North Carolina State University</i> Investigation of intermediate dielectric for dual floating gate MOSFET
P-19	Alex Shukh , <i>Spingate Technology</i> SpinRAM as a Storage Class Memory
P-20	Mike Street , <i>University of Nebraska, Lincoln</i> Tuning the Néel Temperature of Magnetoelectric Chromium Oxide for Voltage-Controlled Spintronics
P-21	Junlei Wang , <i>University of Nebraska, Lincoln</i> Growth and Characterization of Magnetoelectric Fe_2TeO_6 Thin Films
P-22	Yi Wang , <i>University of Nebraska, Lincoln</i> Probing boundary magnetization through exchange bias in heterostructures with competing anisotropy
P-23	Yuhao Wang , <i>Nanyang Technological University</i> Logic-in-memory based Big-data Computing by Nonvolatile Domain-wall Nanowire Devices
P-24	JingPing Xu , <i>Huazhong University of Science and Technology</i> Characteristics of MONOS Nonvolatile Memory with High-k LaYON as Charge Storage Layer
P-25	Xiang Yang , <i>University of Pennsylvania</i> Voltage-Time Invariance in Nanometallic RRAM
P-26	Niannian Yu , <i>Huazhong University of Science and Technology</i> Structural variety of amorphous GeTe ultrathin films
P-27	Zhiyong Zhang , <i>Beijing Microelectronic Technology Institute</i> A super low variable cost Flash Translation Layer for NAND Flash memory
P-28	Hu Zuoqi , <i>Huazhong University of Science and Technology</i> Simulation study on the information storage mechanism of STT-MRAM
P-29	Bin Ma , <i>Fudan University</i> The magnetic properties of perpendicular exchange coupled composite $L1_0\text{-FePt}/[\text{Co}/\text{Ni}]_N$ films

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